TOSHIBA 2SC2459

TOSHIBA TRANSISTOR SILOCON NPN EPITAXIAL TYPE (PCT PROCESS)

2 S C 2 4 5 9

AUDIO AMPLIFIER APPLICATIONS

High Breakdown Voltage : $V_{CEO} = 120 V$ (Max.)

High DC Current Gain : $h_{FE} = 200 \sim 700$

Excellent hFE Linearity

: h_{FE} ($I_C = 0.1 \text{ mA}$) / h_{FE} ($I_C = 2 \text{ mA}$) = 0.95 (Typ.)

: NF = 1 dB (Typ.), 10 dB (Max.)Low Noise

Complementary to 2SA1049.

Small Package.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	120	V
Collector-Emitter Voltage	v_{CEO}	120	V
Emitter-Base Voltage	$V_{ m EBO}$	5	V
Collector Current	$I_{\mathbf{C}}$	100	mA
Base Current	$I_{\mathbf{B}}$	20	mA
Collector Power Dissipation	$P_{\mathbf{C}}$	200	mW
Junction Temperature	$T_{ m j}$	125	°C
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~125	°C

0.55MAX **EMITTER COLLECTOR JEDEC**

2-4E1A

Unit in mm

Weight: 0.13 g

EIAJ TOSHIBA

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 120 \text{ V}, I_{E} = 0$	_	_	0.1	μ A
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 5 V, I_{C} = 0$	_	_	0.1	μ A
DC Current Gain	hFE (Note)	$V_{ m CE}=6 m V,\;I_{ m C}=2 m mA$	200	_	700	
Collector-Emitter Sturation	Van	$I_{\rm C}=10{\rm mA},I_{\rm B}=1{\rm mA}$			0.3	v
Voltage	V _{CE} (sat)	1C = 10 mA, 1B = 1 mA	_	_	0.5	\ \ \
Transition Frequency	${ m f_T}$	$V_{CE} = 6 V, I_{C} = 1 mA$	_	100	_	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 10 \text{ V}, \text{ I}_{E} = 0, \text{ f} = 1 \text{ MHz}$	_	3.0	_	pF
Noise Figure	NF	$V_{CE} = 6 V, I_{C} = 0.1 mA,$		1.0	10	dB
		$f = 1 \text{ kHz}, R_G = 10 \text{ k}\Omega$	_			

(Note): hFE Classification GR: 200~400, BL: 350~700

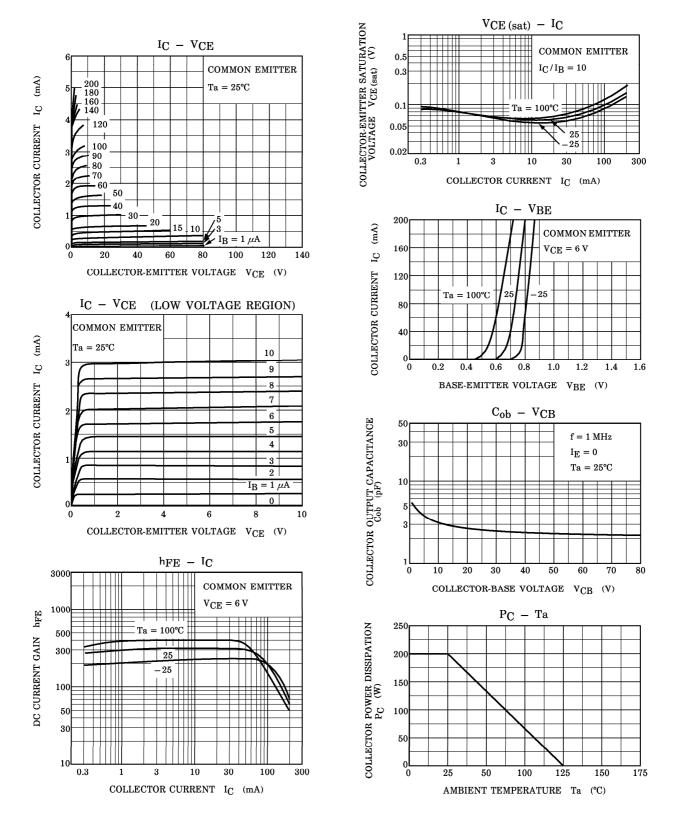
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